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最新トランジスタ規格表 (New Transistor Manual) lists all the transistors registered with the Electronic Industries Association of Japan (EIAJ), arranged in a manner easy to look up. We hope that you will make full use of the data provided in this manual by referring to the Japanese-English translation key given below.

型名	社名	用途	構造	最大定格 ($T_c=25^\circ\text{C}$)					電気的特性 ($T_c=25^\circ\text{C}$)										外形	備考	
				V_{ce0} (V)	V_{ce0} (V)	I_c (mA)	P_c (mW)	T_c ($^\circ\text{C}$)	I_{c0} 最大値 (μA)	直流又はパルス h_{FE}		バイアス		h_{FE}	h_{ie}	h_{re}	h_{re}	h_{oe}			$f_{\alpha b}$
1	2	3	4	5					6		7		8				9		10	11	12

- 1 TYPE NUMBER
- 2 ORIGINAL MANUFACTURER
- 3 USES
- 4 MATERIAL AND STRUCTURE
- 5 MAXIMUM RATINGS
- 6 I_{cB0} MAXIMUM VALUE AND V_{ce} VALUE (CRITERIA FOR MEASURING I_{cB0})
- 7 STANDARD VALUE OF DC/PULSE h_{FE} AND V_{ce} , I_c (CRITERIA FOR MEASURING DC/PULSE h_{FE})
- 8 STANDARD VALUE OF h PARAMETERS AND BIAS V_{ce} , I_E (CRITERIA FOR MEASURING h PARAMETERS)

- * INDICATES VALUE IN GROUNDED-BASE OPERATION, OTHERWISE VALUE IN EMITTER-GROUNDED OPERATION.
- 9 $f_{\alpha b}$ OF RF CHARACTERISTIC, EXCEPT IN CASE OF * WHICH INDICATES VALUE OF f_T .
- 10 C_{ob} AND $r_{bb'}$ OF RF CHARACTERISTICS EXCEPT IN CASE OF * IN $r_{bb'}$ COLUMN WHICH INDICATES VALUE OF h_{ie} (real)
- 11 OUTLINE
- 12 REMARKS

: とコンプリ : COMPLEMENTARY TO

型名	社名	用途	構造	最大定格 (T _a = 25°C)					電 気 的 特 性 (T _a = 25°C)											外 形	備 考			
				V _{CB0} (V)	V _{EB0} (V)	I _C (mA)	P _C (mW)	T _J (°C)	I _{CB0} 最大値 (μA)	V _{CEB} (V)	直流又はパルス hFE		バイアス		h _{fe}	h _{ie}	h _{re}	h _{oe}	f _{0.6}			C _{ob}	r _{bb'}	
2SC1301	富士通	SW	Si.TMe	250	5	30A	200W (T _c =25°C)	175	200	150	40	5	10A	5	-2A	t _{on} <2.5μS, t _f <2.5μS t _{sig} <4μS	25*					191		
" 1302	"	"	"	400	5	30A	200W (T _c =25°C)	175	200	150	25	5	15A	5	-2A	t _{on} <4μS, t _f <2.5μS t _{sig} <4μS	20*					191		
" 1303	松下	PA	Si.EP	40	4	300	600	175	1	20	70	13.5	100	10	-30		700*	6.5	15			84B		
" 1304	日立	"	Si.T	300	5	500	20W (T _c =25°C)	150	I _{CBX} 100	300	60	10	100	10	-50		7*	16	20*			153		
" 1305																								
" 1306	日電	PA	Si.E	65	4	3A	12W (T _c =25°C)	150	10	40	80	10	500	10	-150	P ₀ =5.5W (f=50MHz, V _{cc} =12V, P _i =0.5W)	300*	20				268		
" 1307	"	"	"	70	4	8A	25W (T _c =25°C)	150	20	40	20~150	10	2A	10	-500	P ₀ =15W (f=50MHz, V _{cc} =12V, P _i =3W)	150*	80				268		
" 1308	三洋	SW	Si.TMe	1500	6	7A	50W (T _c =25°C)	150	100	100	>3	5	4A			t _r <1.4μS						102	水平偏用	
" 1309	三菱	SW	Si.Eme	1200	6	5A	80W (T _c =25°C)	150	1mA	1200	20	10	5A			t _r <1.5μS, t _f <3μS t _{sig} <2μS						102		
" 1310	"	RF. AF. LN SW	Si.EP	30	4	100	200	125	0.1	25	250	6	1	6	-1		8500	0.6	40	150*	2.5	C _c r _{bb'} 200pS	175	
" 1311	"	RF. AF. SW	"	30	4	100	200	125	0.1	25	250	6	1	6	-1		8500	0.6	40	150*	2.5	C _c r _{bb'} 200pS	175	
" 1312	"	RF. AF. LN	"	35	4	100	200	125	0.1	25	500	6	1	6	-1		19k	1.3	22	150*	2.5	C _c r _{bb'} 230pS	138B	
" 1313	"	"	"	50	4	100	200	125	0.1	50	350	6	1	6	-1		19k	1.3	22	150*	2.5	C _c r _{bb'} 230pS	138B	
" 1314	"	PA	"	40	4.5	5A	45W (T _c =25°C)	175	2mA	15	30	10	200			P ₀ =34W (f=175MHz, V _{cc} =13.5V, P _i =9W)						127		
" 1315	"	"	"	35	4.5	500	4W (T _c =25°C)	175	50	15	50	10	100			P ₀ =0.5W (f=150MHz, V _{cc} =13.5V, P _i =0.2W)						84B		
" 1316	ソニー	PA.SW	Si.TMe	750	10	1A	23W (T _c =25°C)	120	200	50	8	3	2A	10	-200		8.5*	120	C _c r _{bb'} 410pS	9		100		
" 1317	松下	PA	Si.EP	30	5	500	400	125	0.1	20	160	10	150	10	-50				200*	6	3.5*	138	2SA719 とコンパリ	
" 1318	"	"	"	60	5	500	400	125	0.1	20	160	10	150	10	-50				200*	6	3.5*	138	2SA720 とコンパリ	
" 1319	日電	RF	Si.P	40	4	25	250	125	0.1	20	90	10	3	10	-3				600*	1.2	C _c r _{bb'} 12pS	138	フォワード AGC	
" 1320	"	"	Si.E	50	4	30	250	125	0.1	20	100	10	10	10	-10				850*	1.4	C _c r _{bb'} 12pS	138		
" 1321	"	RF. Conv. Mix. Osc.	"	30	4	10	100	125	0.1	25	80	6	2	6	-2				900*	1.3	C _c r _{bb'} <20pS	176		
" 1322	富士通	SW	Si.TMe	250	5	15A	100W (T _c =25°C)	175	100	150	50	5	5A	5	-1A	t _{on} <1μS, t _f <1.5μS t _{sig} <4μS	27*					101		
" 1323	三菱	PA	Si.EP	30	4	500	5W (T _c =25°C)	175	50	15	70	15	30			PG=14.2dB (f=220MHz, I _C =30mA, V _{cc} =13.5V)						272		
" 1324	"	"	"	35	4	150	800	175	50	25	70	10	30			G ₀ =10dB (f=770MHz, I _C =30mA, V _{cc} =15V)						85B		
" 1325	日電	SW	Si.TMe	1500	6	6A	80W (T _c =25°C)	150	20	1000	19	15	1A			t _r <2.5μS, t _f <1μS, t _{sig} <1.5μS						102		
" 1326	松下	PA	Si.EP	55		400	5W (T _c =25°C)	175	I _{CB0} 20	V _{CEB} 28	30	5	50	15	-25	P ₀ >1W (f=400MHz, V _{cc} =28V, P _i =0.1W)	700*	<3				84B		
" 1327	"	RF. LN	"	35	5	50	150	125	0.1	10	540	5	2	5	-2		5500	0.4	25	250*	2.2	70	138	2SA721 とコンパリ
" 1328	"	"	"	55	5	50	150	125	0.1	10	540	5	2	5	-2		5500	0.4	25	250*	2.2	70	138	2SA722 とコンパリ
" 1329	日電	RF	Si.E	50	5	8A	60W (T _c =25°C)	200	2mA	30	100	10	5A			P ₀ =32W (f=70MHz, V _{cc} =12V, P _i =8W)						149		
" 1330	"	RF. AF	"	50	5	100	400	125	0.1	40	150	6	1	6	-1		4800	4.5	17	250*	4.5	25*	44	